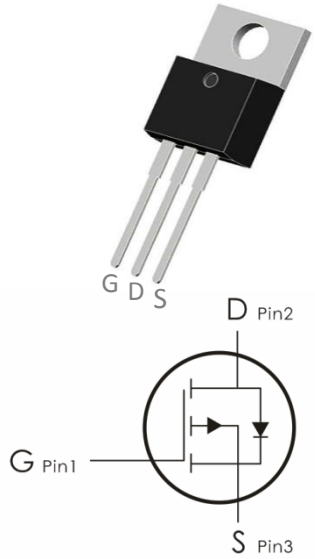
Description：

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.



Features：

1) V_{DS}=-100V,I_D=-12A,$R_{DS(ON)}$<200mΩ @V_{GS}=-10V
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
DOP12P10	12P10	TO- 220	50 pcs/Tube

Absolute Maximum Ratings： (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current-[1]	-12	A
	Continuous Drain Current-TC=100℃	-9.2	
	Pulsed Drain Current[2]	-52	
E_{AS}	Single Pulse Avalanche Energy[3]	65	mJ
P_D	Power Dissipation[4]	40	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case(Note 2)	3.13	℃/W
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient[1]	---	

Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	-100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=-100V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±10	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	-1	-1.9	-3	V
$R_{DS(ON)}$	Drain-Source On Resistance[2]	V_{GS}=-10V,I_D=16A	---	170	200	mΩ
		V_{GS}=-4.5V,I_D=A	---	---	---	
G_{FS}	Forward Transconductance	$V_{DS=}$-50V, I_D=-10A	12	---	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-25V, V_{GS}=0V, f=1MHz	---	760	---	pF
C_{oss}	Output Capacitance		---	260	---	
C_{rss}	Reverse Transfer Capacitance		---	170	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=-50V, I_D=10A, R_{GEN}=9.1Ω .V_{GS}=-10V	---	14	---	ns
t_r	Rise Time		---	18	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	50	---	ns
t_f	Fall Time		---	18	---	ns
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-50V, I_D=-10A	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	7	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage[2]	V_{GS}=0V,I_S=10A	---	---	-1.2	V
Is	Diode Forward Current (Note 2)	VD=VG=0V	---	---	-13	A
Trr	Reverse Recovery Time	TJ = 25°C, IF =-10A di/dt = 100A/ s(Note3)	---	35	---	nS
Qrr	Reverse Recovery Charge		---	46	---	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition：Tj=25℃,V_{DD}=-50V,V_G=-10V,L=0.5mH,Rg=25Ω

Typical Characteristics：

(T_C=25℃ unless otherwise noted)

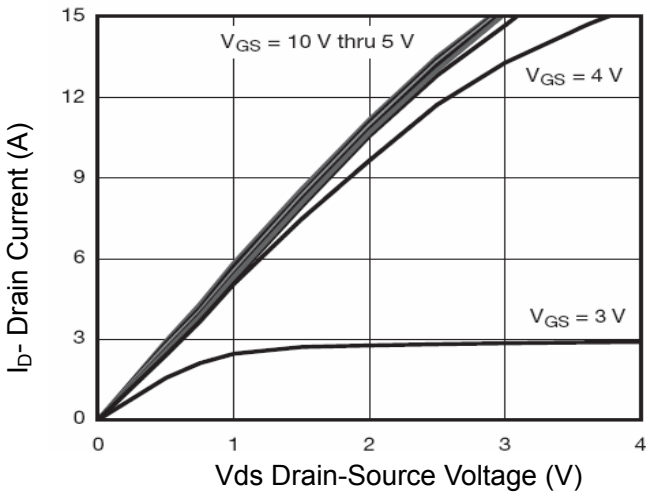


Figure 1 Output Characteristics

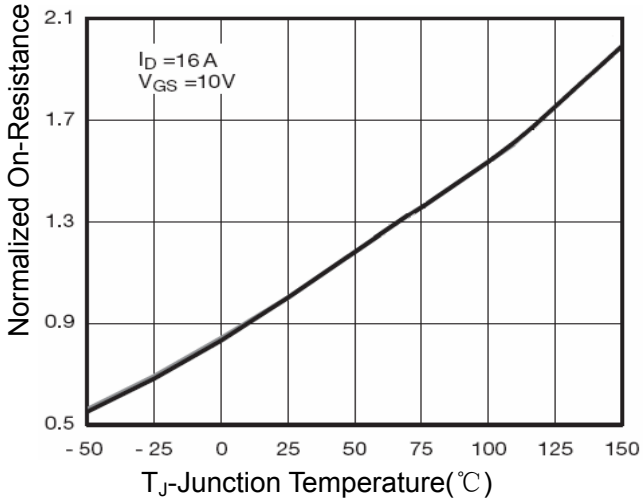


Figure 4 Rdson-JunctionTemperature

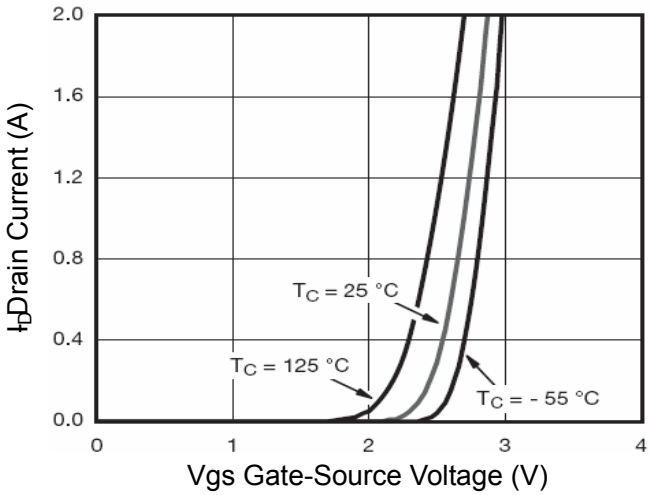


Figure 2 Transfer Characteristics

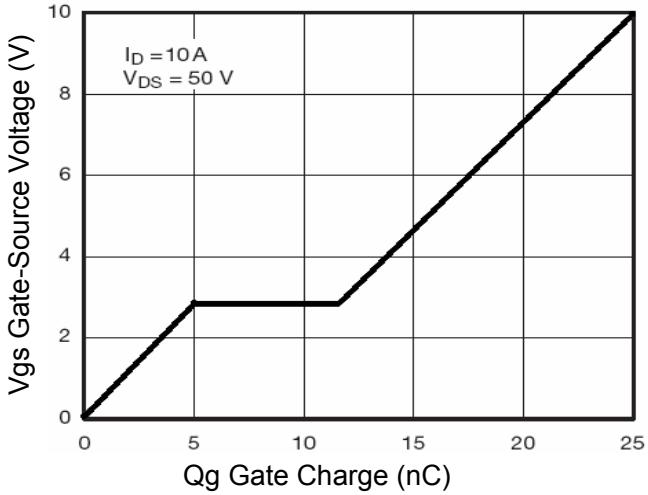


Figure 5 Gate Charge

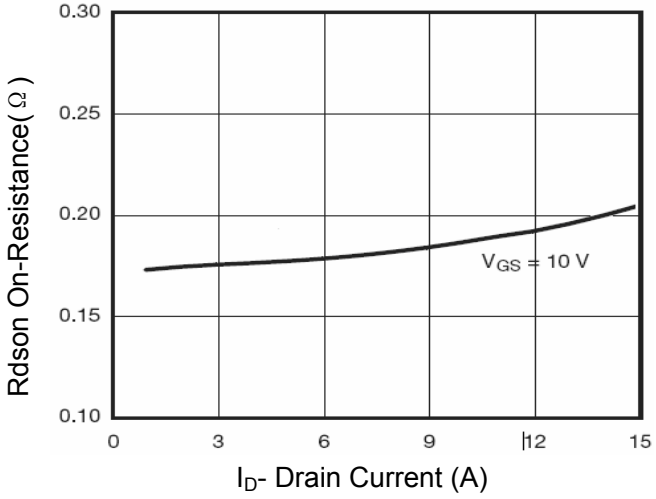


Figure 3 Rdson- Drain Current

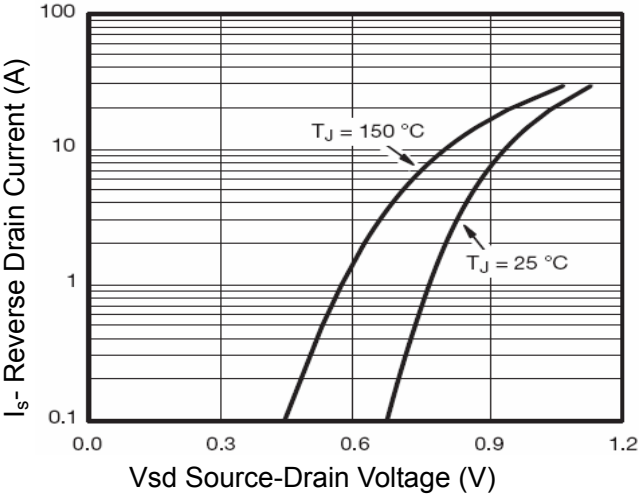
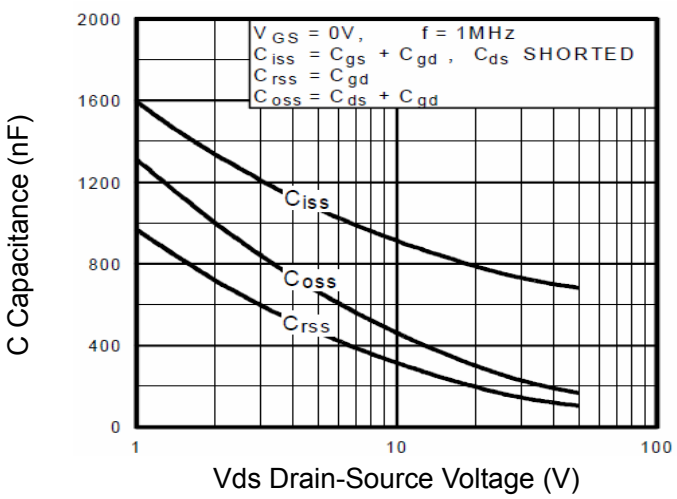


Figure 6 Source- Drain Diode Forward



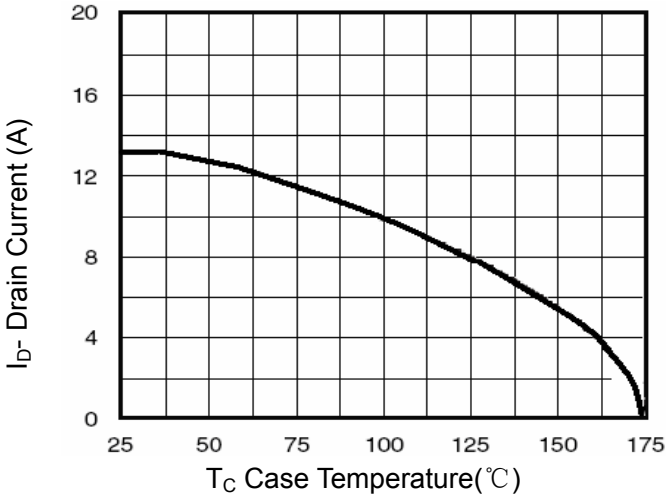


Figure 7 Capacitance vs Vds

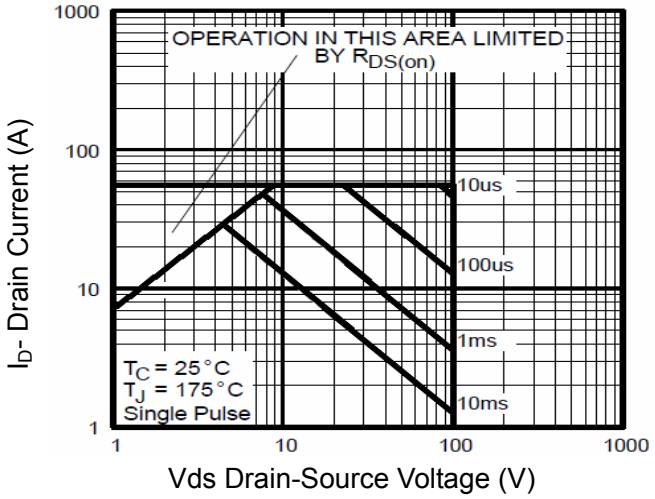


Figure 8 Safe Operation Area

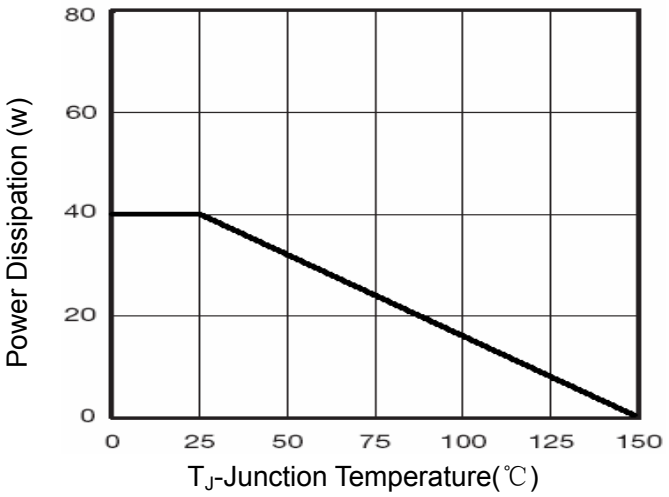


Figure 10 Power De-rating

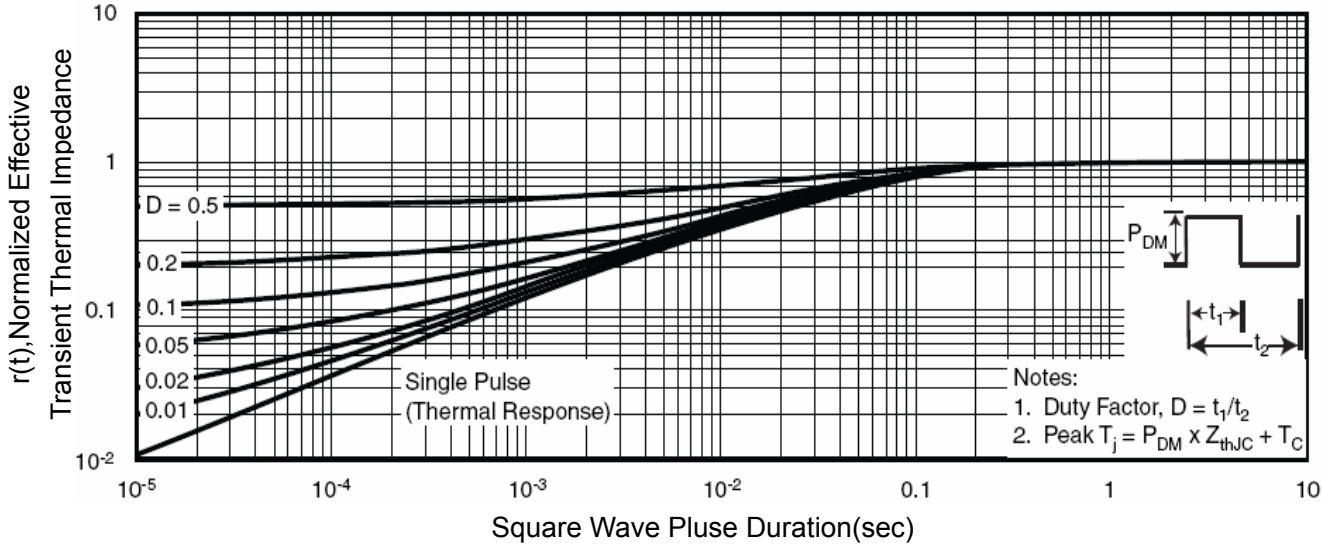
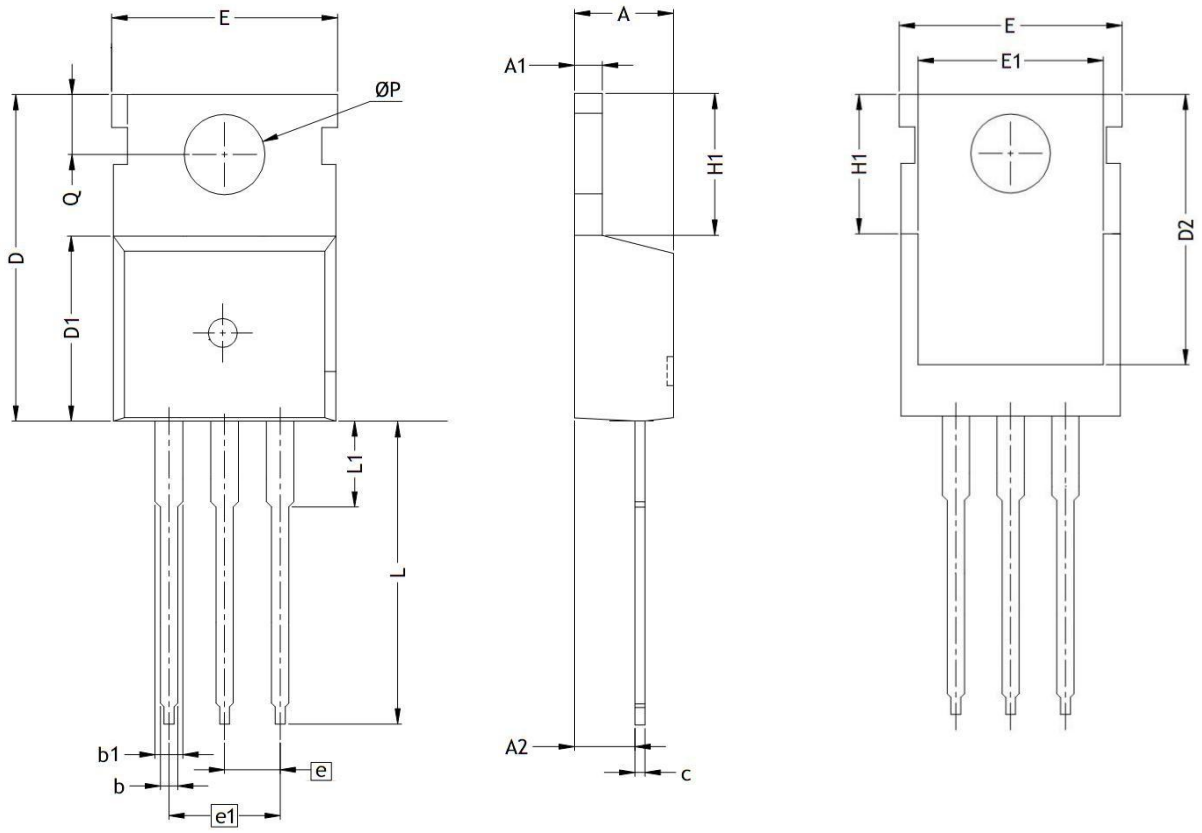


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220 Package Information：



UNIT：mm

SYMBOLS	A	A1	A2	b	b1	c	D	D1	D2	E	E1	e
MIN	4.25	1.25	2.35	0.7	1.15	0.45	14.35	8.80	13.05	9.90	7.85	2.540
MAX	4.65	1.35	2.55	0.9	1.75	0.60	15.95	9.50	13.65	10.35	8.85	BSC
SYMBOLS	e1	H1	L	L1	Q	ϕP						
MIN	5.080	6.30	12.85	2.85	2.70	3.50						
MAX	BSC	6.65	13.50	3.25	2.90	3.70						

Marking Information：

①. Doingter LOGO

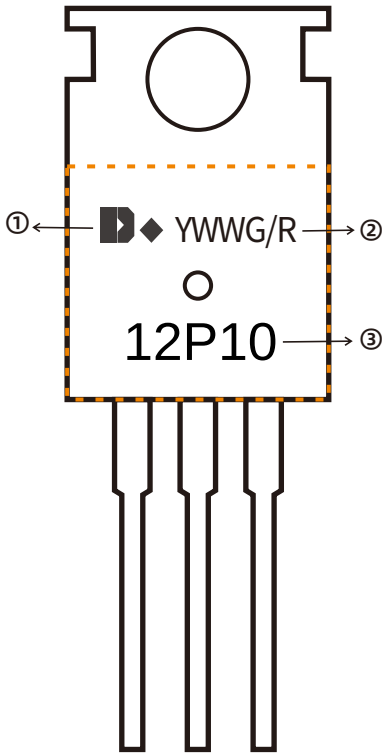
②. Date Code(YWWG / R)

Y：Year Code，last digit of the year

WW：Week Code(01-53)

G/R：G(Green) /R(Lead Free)

③. Part NO.



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